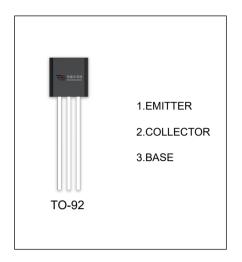


KTA1270 TRANSISTOR (PNP)

FEATURES

General Purpose Application Switching Application



ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
KTA1270	TO-92	Bulk	1000pcs/Bag
KTA1270-TA	TO-92	Таре	2000pcs/Box

MAXIMUM RATINGS (T_a =25 $^{\circ}$ C unless otherwise noted)

Symbol	Parameter	Value	Unit	
V _{CBO}	Collector-Base Voltage	-35	V	
V _{CEO}	Collector-Emitter Voltage	-30	V	
V _{EBO}	Emitter-Base Voltage	-5	V	
Ic	Collector Current -Continuous	-500	mA	
P _D	Collector Power Dissipation	500	mW	
R _{θ JA}	Thermal Resistance from Junction to Ambient	250	°C /W	
T _J ,T _{stg}	Operation Junction and Storage Temperature Range	-55~+150 ℃		



Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = -100μA, I _E =0	-35			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = -1mA , I _B =0	-30			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = -100μA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} = -35 V , I _E =0			-0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} = -5 V , I _C =0			-0.1	μA
DC comment spin	h _{FE1}	V _{CE} =-1 V, I _C = -100mA	70		240	
DC current gain	h _{FE2}	V _{CE} =-6 V, I _C = -400mA	25			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = -100mA, I _B = -10mA			-0.25	V
Base-emitter voltage	V _{BE(on)}	V _{CE} = -1V, I _C = -100mA			-1	V
Transition frequency	f _T	V _{CE} =-6 V, I _C = -20mA f =100MHz		200		MHz
Collector output capacitance	C _{ob}	V _{CB} =-6V,I _E =0,f=1MHz		13		pF

CLASSIFICATION OF h_{FE}

Rank		0	Y
Panga	h _{FE(1)}	70-140	120-240
Range	h _{FE(2)}	25(min)	40(min)